/ Descriptions

TO-220F

Schottky Barrier Diode in a TO-220F Plastic Package.

/ Features

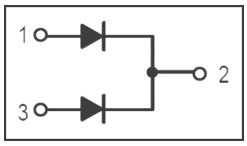
Low forward voltage drop,low power losses,High efficiency operation.

/ Applications

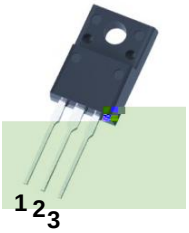
OR-ing DC-DC

For use in high frequency inverters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

/ Equivalent Circuit



/ Pinning



PIN1 Anode PIN 2 Cathode PIN 3 Anode

/ h_{FE} Classifications & Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RM} V_{RSM} V_{DC}	200	V
RMS Voltage	V_{RMS}	140	V
Average Rectified Forward Current	$I_{F(AV)}$	2 × 5	A
Non Repetitive Peak Surge Current	I_{FSM}	80	A
Thermal Resistance Junction to Case	$R_{\theta Jc}$	4.5	/W
Junction and Storage Temperature Range	T_j T_{stg}	-40 +150	

A Electrical Charactertings(Ta= 5

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Breakdown Voltage	V_{BR}	I_R=1mA(Ta=25)	200			V
Forward Voltage	V_F	I_F =2.5A(Ta=25)		0.81	0.95	V
		I_F =2.5A(Ta=125)		0.62	0.75	V
		I_F =5A(Ta=25)		1.10	1.60	V
		I_F =5A(Ta=125)		0.70	0.75	V
Instantaneous Reverse Current	I_R Note 1	V_R=200V(Ta=25)			50	μA
		V_R=200V(Ta=125)		1.5	10	mA

/Notes

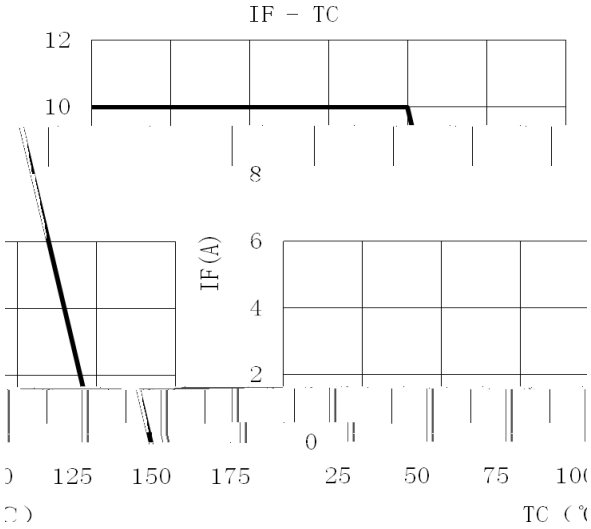
1.

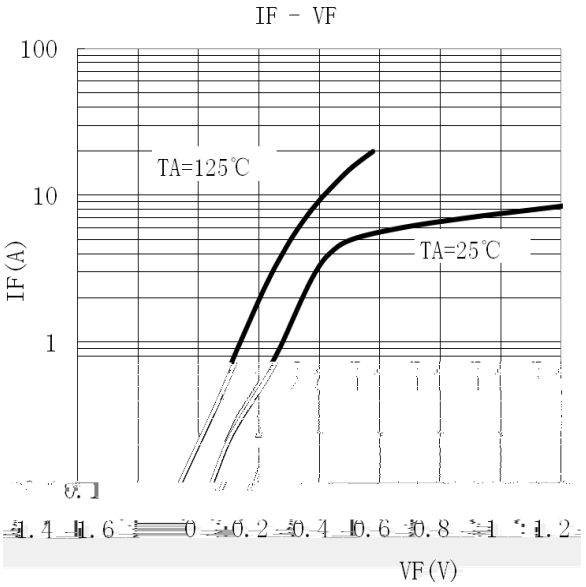
Short duration pulse test used to minimize self-heating effect.

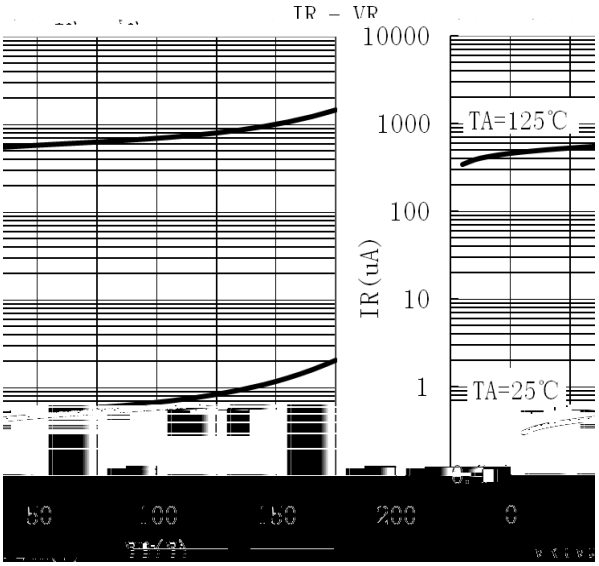
2.

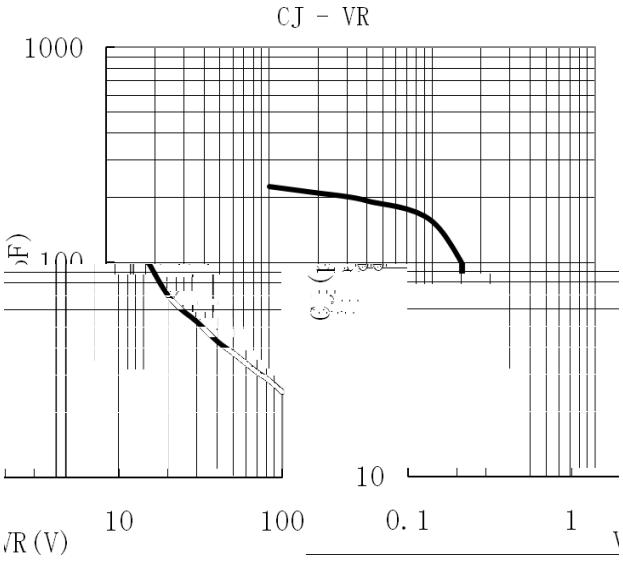
Unless otherwise noted, values for the parameters of a single chip

/ Electrical Characteristic Curve

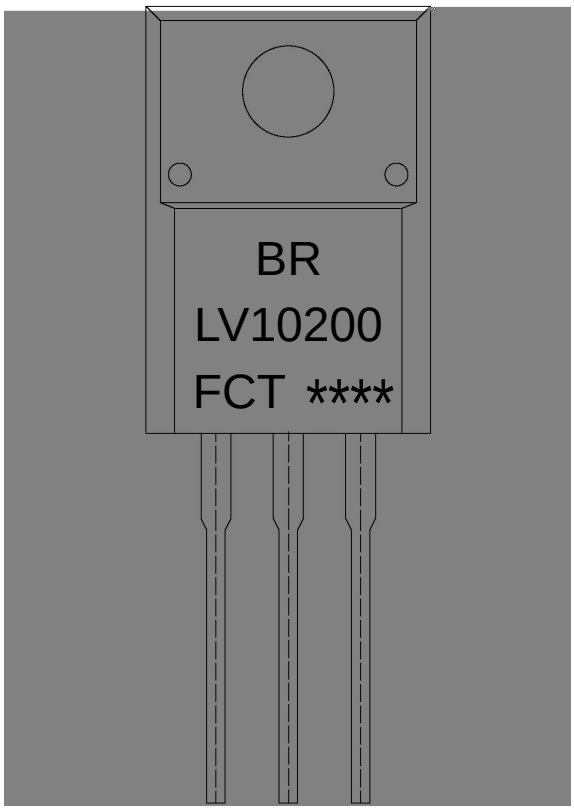








/ Marking Instructions



BR

LV10200

F:

CT:

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Note:

BR:	Company Code
LV10200:	Product Type Code.
F	Package Code
CT:	Internal Structure
****:	Lot No. Code, code change with Lot No.